

SiBP28/4-5FX

Features

- High precision
- MEMS process
- High performance, shielded, Micro-Cavity structure
- Silicon base, 50 Ω CPW output
- Au bonding for MCM application

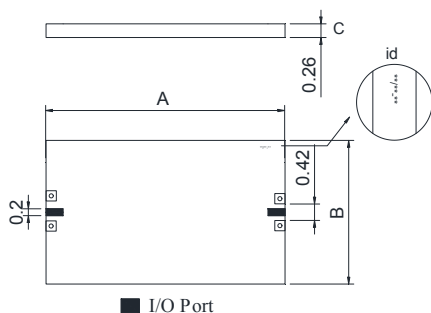
Electrical Parameter

Operating Temperature	-55°C ~ +70°C
Storage Temperature	-65°C ~ +125°C
Highest Input Power	35dBm

Electrical Specifications (TA=+25°C)

Item	Min.	Typical	Max.	Unit
Central Frequency(f ₀)	-	28	-	GHz
Passband Frequency Range	26	-	30	GHz
Passband Ripple	-	-	1	dB
Central Insertion Loss	-	1.1	-	dB
Return Loss	-	17	-	dB
Out Band Attenuation	≥30@23.4GHz			dB
	≥30@32.6GHz			dB

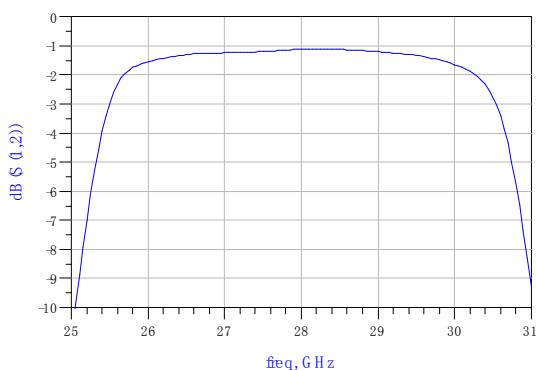
Overall Dimension



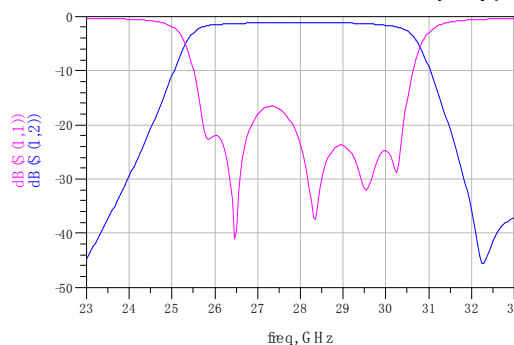
Dimension Symbols	Value (mm)		
	Min.	Nominal	Max.
A	2.9	-	3.0
B	1.8	-	1.9

Typical Testing Curve

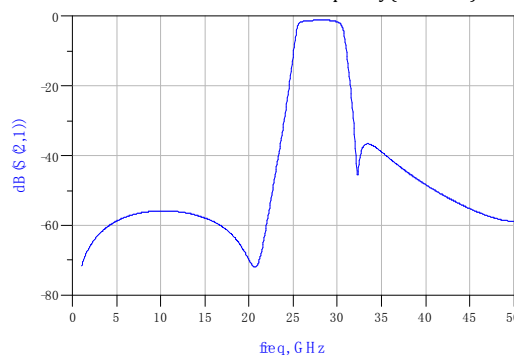
Passband Loss VS Frequency (TA=25°C)



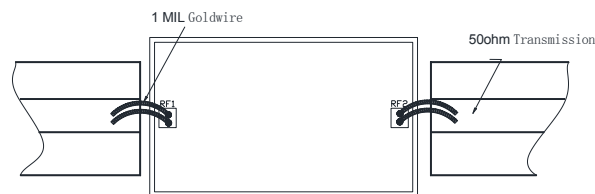
Out Band Attenuation & Return Loss VS Frequency (TA=25°C)



Far-end Attenuation VS Frequency (TA=25°C)



Assembly Diagram



Note:

- Au bonding ribbon width=150um,thickness=12.5um, as short as possible.
- Recommended space between chip and cover:1-3mm
- Low temperature assembly technology:180°C Max
- The center RF stripline of CPW can be connected directly to the microstrip line of customer.
- Top surface bonded to Ground is helpful for high l stopband rejection.
- Underlayered metal: Cova (recommended).

